

COMPUTER DIODE

200mA

Low Power, Switching

1N3600; JAN, JANTX & JANTXV 1N3600
 1N4150; JAN, JANTX & JANTXV 1N4150
 JAN, JANTX & JANTXV 1N4150-1

FEATURES

- Metallurgical Bond
- Qualified to MIL-S-19500/231
- Planar Passivated Chip
- DO-7 or DO-35 Package
- Non-JAN Available

DESCRIPTION

This series of switching diodes is useful in many computer switching applications, for both military and commercial systems.

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ABSOLUTE MAXIMUM RATINGS, AT 25°C

Reverse Breakdown Voltage	75V
Peak Working Voltage	50V
Average Output Current	200mA
Surge Current (1sec)	0.5A
(1μsec)	4.0A
Operating Temperature Range	-65°C to +175°C
Storage Temperature Range (1N4150)	-65°C to +200°C
(1N3600)	-65°C to +175°C

MECHANICAL SPECIFICATIONS

J, JTX & JTXV 1N3600		J, JTX & JTXV 1N4150, 1N4150-1																					
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DO-7 1N3600	DO-35 1N4150

Microsemi Corp.
Watertown
 The diode experts

ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Characteristics	Forward Voltage	Forward Voltage	Forward Voltage	Forward Voltage	Forward Voltage	Reverse Breakdown Voltage
Conditions	V_{F1} $I_F = 1 \text{ mAdc}$	V_{F2} $I_F = 10 \text{ mAdc}$	V_{F3} $I_F = 50 \text{ mAdc}$ (pulse)	V_{F4} $I_F = 100 \text{ mAdc}$ (pulse)	V_{F5} $I_F = 200 \text{ mAdc}$ (pulse)	BV $I_R = 5.0 \text{ }\mu\text{Adc}$
Minimum	0.540 Vdc	0.660 Vdc	0.760 Vdc	0.820 Vdc	0.870 Vdc	75 Vdc
Maximum	0.620 Vdc	0.740 Vdc	0.860 Vdc	0.920 Vdc	1.00 Vdc	—

Characteristics	Reverse Current	Reverse Current	Junction Capacitance	Reverse Recovery Time	Reverse Recovery Time	Forward Recovery Time
Conditions	I_R $V_R = 50 \text{ Vdc}$	I_R $V_R = 50 \text{ Vdc}$ $T_A = 150^\circ\text{C}$	C $V_R = 0$ F = 1 MHz $V_{sig} = 50 \text{ mv (p-p)}$	t_{rr1} $I_F = I_R =$ 10 to 200 mAdc; $R_L = 100 \text{ ohms}$	t_{rr2} $I_F = I_R =$ 200 to 400 mAdc; $R_L = 100 \text{ ohms}$	t_{fr} $I_F = 200 \text{ mAdc};$ $t_p = 100 \text{ nsec};$ $t_r = 0.4 \text{ nsec}$
Maximum	0.1 μAdc	100 μAdc	2.5 pf	4 nsec	6 nsec	10 nsec

